

**FEATURES**

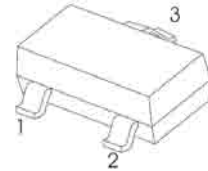
- Complementary to MMBT3906

**MARKING:1AM**

**SOT - 23**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	200	mA
P <sub>C</sub>	Collector Power Dissipation	200	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C
T <sub>OPR</sub>	Operating Temperature	0~+70	°C



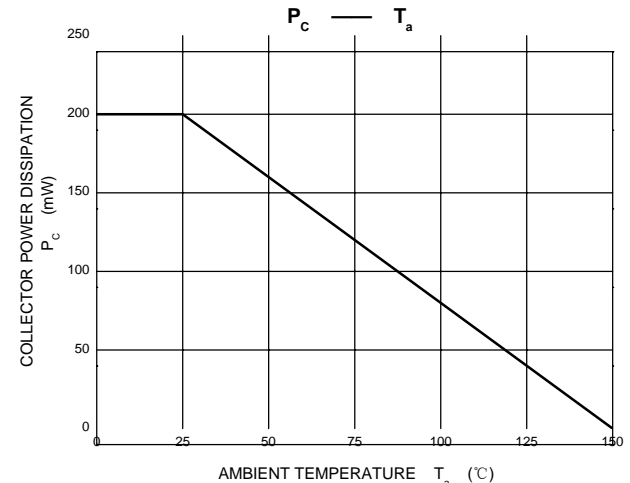
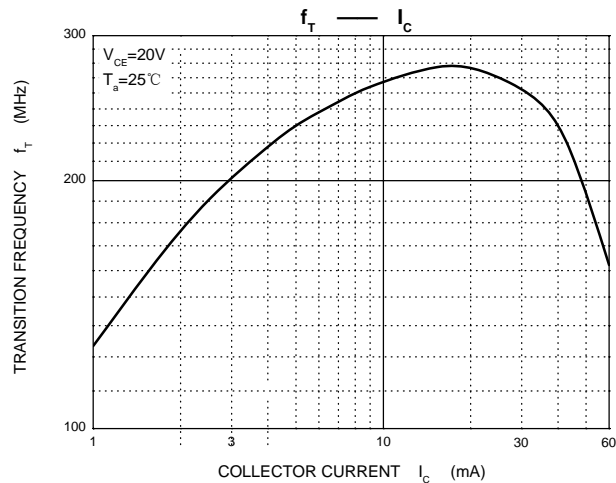
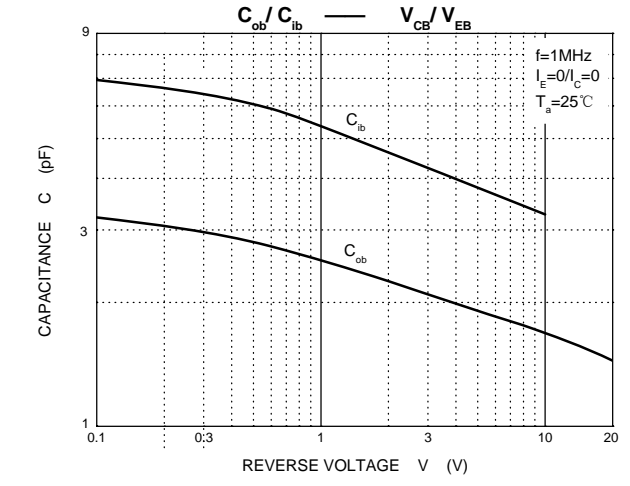
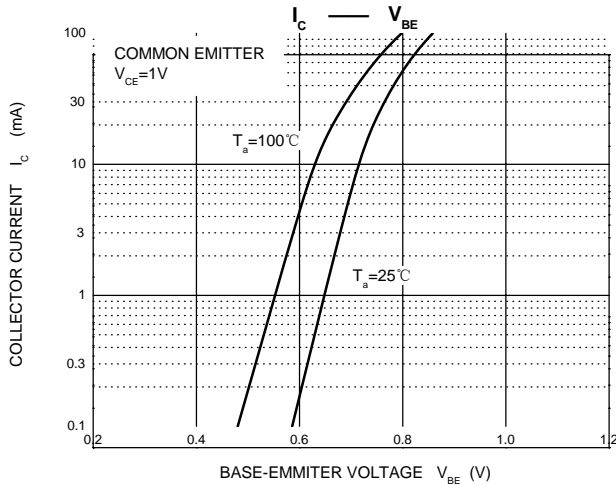
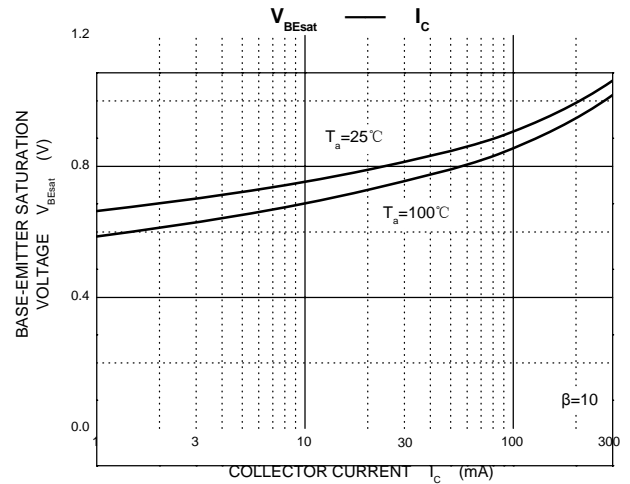
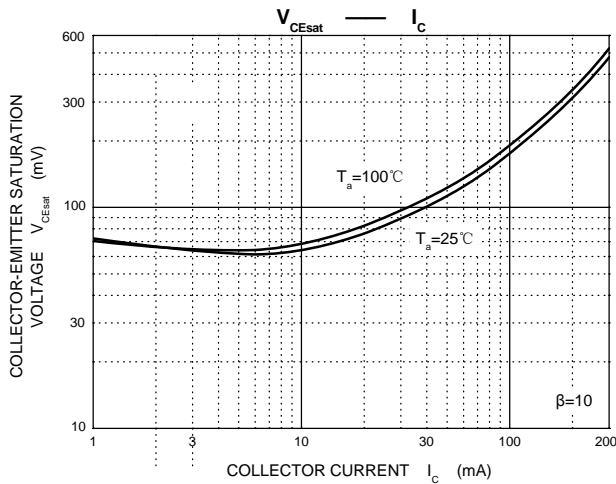
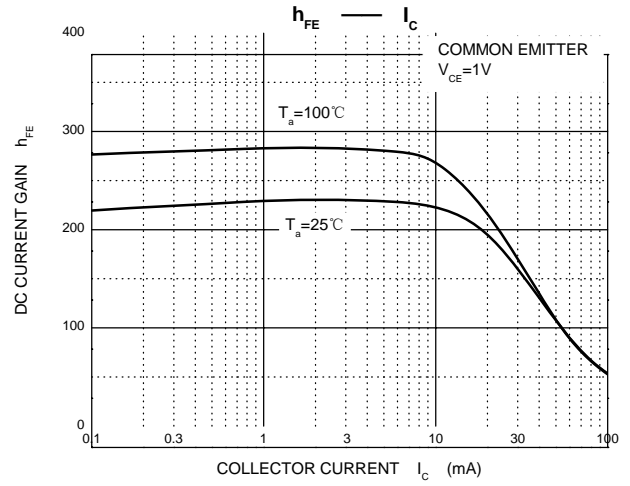
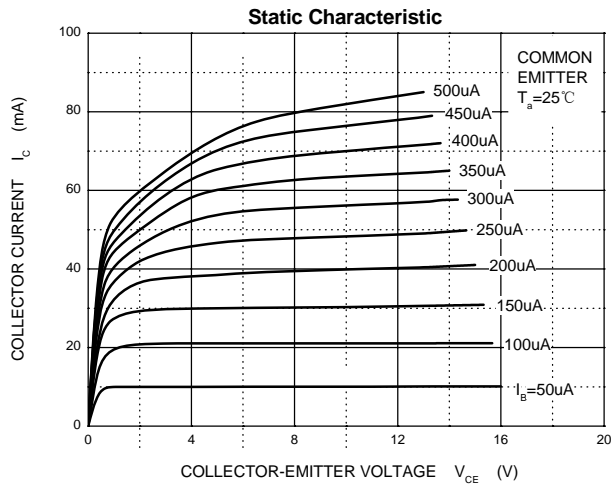
1. BASE
2. EMITTER
3. COLLECTOR

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

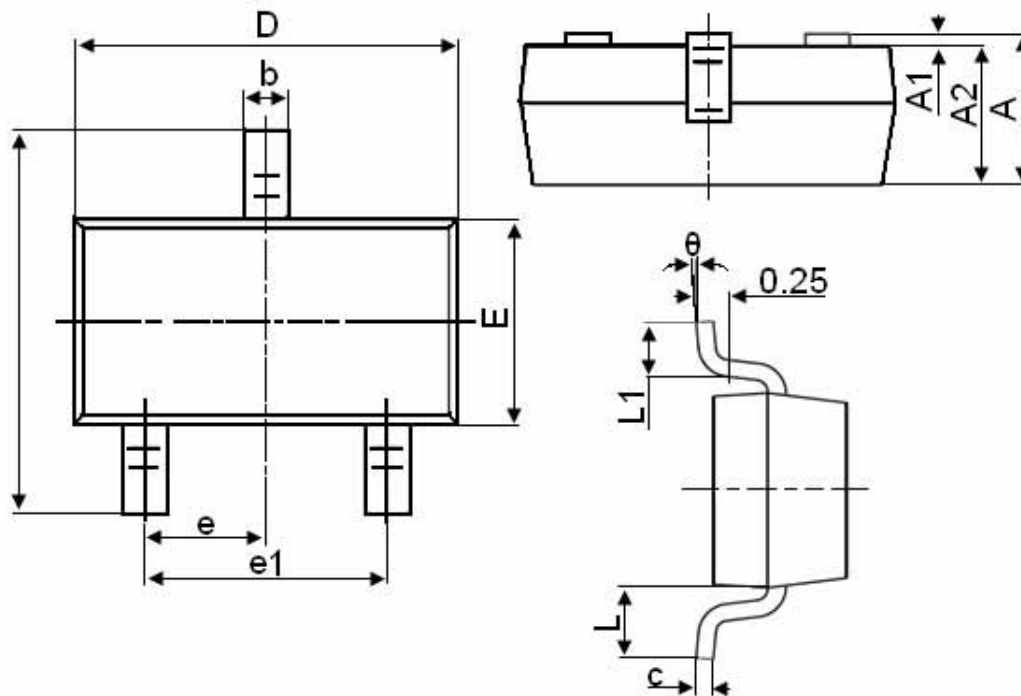
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =30V, V <sub>EB(off)</sub> =3V			50	nA
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 60V, I <sub>E</sub> =0			100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			100	nA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA	100		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =50mA	60			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.95	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=100MHz	300			MHz
Delay time	t <sub>d</sub>	V <sub>CC</sub> =3V, V <sub>BE(off)</sub> =-0.5V I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA			35	ns
Rise time	t <sub>r</sub>	V <sub>CC</sub> =3V, V <sub>BE(off)</sub> =-0.5V I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA			35	ns
Storage time	t <sub>s</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA, I <sub>B1</sub> = I <sub>B2</sub> =1mA			200	ns
Fall time	t <sub>f</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA, I <sub>B1</sub> = I <sub>B2</sub> =1mA			50	ns

**CLASSIFICATION OF h<sub>FE(1)</sub>**

HFE	100-300	
RANK	L	H
RANGE	100 - 200	200 - 300



**SOT-23 Package Information**



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

**Notes**

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.